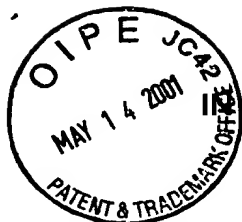


GP 1782



THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT

APPLICANTS: Fuchs et al.

SERIAL NO.: 09/764,950 GROUP ART UNIT: 1762

FILED: January 17, 2001

TITLE: "METHOD FOR IMPROVING THE OPTICAL SEPARATION OF
FLUORESCENT LAYERS"

Assistant Commissioner for Patents,

Washington, D.C. 20231

RECEIVED

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S I R:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the following documents be made during the course of examination of the above-referenced application for United States Letters Patent.

- AA United States Patent No. 3,825,763
- AL German OS 198 52 326
- AM German PS 195 16 450
- AN German PS 42 19 347
- AO European Application 0 698 932
- AP European Application 0 175 578
- AR Vapour-Deposited CsI:Na Layers, I. Morphologic and Crystallographic Properties, Stevels et al., Philips Res. Repts. 29 (1974) pp. 340-352
- AS Vapour-Deposited CsI:Na Layers, II. Screens for Application in X-ray Imaging Devices, Stevels et al., Philips Res. Repts. 29 (1974) pp. 353-362
- AT Computersimulation des Photonentransports in CsI-Eingangsschirmen von Röntgenbildverstärkern, Eckenbach, Unsere Forschung in Deutschland (Philips) Vol. IV (1989) pp 51-53

AU Effect of the Mobility of Metal Atoms on the Structure of Thin Films Deposited at Oblique Incidence, van de Waterbeemd et al., Philips Res. Repts. Vol. 22 (1967) pp. 375-387

AV Evolutionary Selection, A Principle Governing Growth Orientation in Vapour-Deposited Layers, van der Drift, Philips Res. Repts. Vol. 22 (1967) pp. 267-268

EXPLANATION OF RELEVANCE

References AA, AL, AM, AN and AO were cited in a Search Report rendered by the German Patent and Trademark Office during examination proceedings for the German application corresponding to the present United States application. English translations of References AL, AM and AN are not readily available to the Applicants, however, each of those references has an English-language Abstract attached thereto. These references also were identified and discussed in the last paragraph on page 3 and in the first paragraph on page 4 of the present specification.

References AR, AS, AT and AU also were identified and discussed in the introductory portion of the present specification. An English translation of Reference of AT is not readily available to the Applicants, however, Applicants stand by the statements in the specification concerning the teachings of that reference.

Reference AV is further reference known to the Applicants describing growth orientation which takes place in vapor-deposited layers.

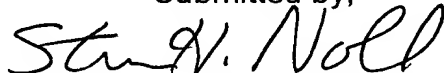
Copies of each of the above references together with Form 1449 are submitted herewith.

As of the date of mailing of this Information Disclosure Statement, a first Office

therefore, this Information Disclosure Statement is in compliance with 37 C.F.R. §1.97(b)(3), and no fee is necessary.

All claims of the application are submitted to be patentable over the teachings of the above references, taken singly or in combination. Early consideration of the application is therefore respectfully requested.

Submitted by,



(Reg. 28,982)

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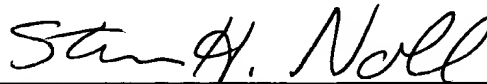
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on May 10, 2001.



STEVEN H. NOLL